



Shantou Huashan Electronic Devices Co.,Ltd.

PNP DIGITAL TRANSISTOR

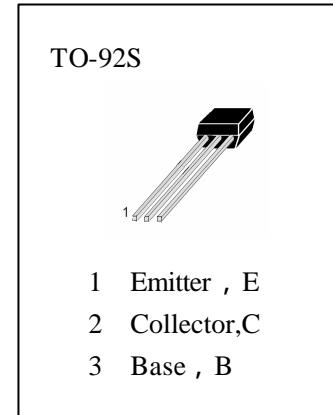
**HA144E**

## APPLICATIONS

Switching Circuit , Interface Circuit.

## ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ C$ )

$T_{stg}$	Storage Temperature.....	-55~150
$T_j$	Junction Temperature.....	150
$P_c$	Collector Dissipation.....	300mW
$V_{CBO}$	Collector-Base Voltage.....	-50V
$V_{CEO}$	Collector-Emitter Voltage.....	-50V
$V_{EBO}$	Emitter-Base Voltage.....	-10V
$I_c$	Collector Current.....	-100mA



## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-50			V	$I_C=-10 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	-50			V	$I_C=-0.1mA, I_B=0$
ICBO	Collector Cut-off Current			-0.1	$\mu A$	$V_{CB}=-40V, I_E=0$
ICEO	Collector Cut-off Current			-0.5	$\mu A$	$V_{CE}=-40V, I_B=0$
IEBO	Emitter Cut-off Current	-30	-53	-80	$\mu A$	$V_{EB}=-5V, I_C=0$
HFE	DC Current Gain	70				$V_{CE}=-5V, I_C=-5mA$
VCE(sat)	Collector- Emitter Saturation Voltage		-0.1	-0.3	V	$I_C=-10mA, I_B=-0.5mA$
VI ( off )	Input Off Voltage	-0.8	-1.1	-1.5	V	$V_{CE}=-5V, I_C=-0.1mA$
VI ( on )	Input On Voltage	-1.0	-2.5	-5.0	V	$V_{CE}=-0.2V, I_C=-5mA$
R1	Input Resistor	32	47	62	Kohm	
R2/ R1	Resistance Ratio	0.9	1.0	1.1		
fr	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=-10V, I_C=-5mA$
Cob	Output Capacitance		3.7		pF	$V_{CB}=-10V, f=1MHz$